

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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MAR 15 2004 JC88
PATENT & TRADEMARK OFFICE

In re Application of:)	Examiner: Unassigned
)	
Pravin K.Narwankar, et al.)	Art Unit: Unassigned
)	
Serial No. 10/772,893)	
)	
Filed: February 4, 2004)	
)	
For: Tailoring Nitrogen Profile In Silicon)	
Oxynitride Using Rapid Thermal)	
Annealing With Ammonia Under)	
Ultra-Low Pressure)	

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search

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has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

X 37 C.F.R. §1.97(b).

 37 C.F.R. §1.97(c). If so, then enclosed with this Information Disclosure Statement is one of the following:

 A statement pursuant to 37 C.F.R. §1.97(e) or

 A check for \$180.00 for the fee under 37 C.F.R. § 1.17(p).

 37 C.F.R. §1.97(d). If so, then enclosed with this Information Disclosure Statement are the following:

(1) A statement pursuant to 37 C.F.R. §1.97(e); and

(2) A check for \$180.00 for the fee under 37 C.F.R. §1.17(p) for submission of the Information Disclosure Statement.

If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP



Dated: March 10, 2004

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Substitute for Form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)



Sheet		of		Attorney Docket Number	008209/USA/FEP/GCM/RKK
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ITO, T., et al., "Direct Thermal Nitridation of Silicon Dioxide Films In Anhydrous Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Optical Properties, Vol. 127, No. 9, September 1980, pages 2053-2057,	
		ITO, T., et al., "Retardation of Destructive Breakdown of SiO ₂ Films Annealed in Ammonia Gas," J. Electrochem Soc.: Solid-State and Technology/Ammonia Gas, Vol. 127, No. 10, September 1980, pages 2248-2251,	
		LEK, C. M., et al., "Impact of Decoupled Plasma Nitridation of Ultra-Thin Gate Oxide on the Performance of P-Channel MOSFETs," Institute of Physics Publishing, Semicond. Sci. Technol., Vol. 17, 2002, pages L25-L28.	

Examiner Signature		Date Considered	
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*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.

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